NSN 5962-01-381-7617

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-381-7617

1.2 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Wgu-2c/b guid e/i fscm 96214

Features Provided:

Programmed and tested to mil-std-883

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Complementary-metal oxide-semiconductor logic

Input Circuit Pattern:

22 input

Case Outline Source And Designator:

D-9 mil-m-38510

Current Rating Per Characteristic:

16.00 milliamperes forward current, nonrepetitive, peak total value

Terminal Surface Treatment:

Solder

Product Name:

Programmable array logic, altered

Voltage Rating And Type Per Characteristic:

-2.0 volts absolute input and 7.0 volts absolute input

Time Rating Per Chacteristic:

30.00 nanoseconds af output megawatts

Memory Device Type:

Pal

Hybrid Technology Type:

Monolithic

Special Features:

One-time programmable

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

24 printed circuit

Specification Data:

67268-5962-8867002la government standard

Departure From Cited Designator:

Programmed per: 704as11592-102 or 1711592-10 (96214)

NSN 5962-01-381-7617

Memory Microcircuit - Page 2 of 2



_					
•	n	0 1	•	12	e:

N/a

Unit Of Measure:

--

Demilitarization:

Yes - demil/mli

Fiig:

A458a0